Contact sales@powerx-ic.com for Full Datasheet

POWER X
博尔芯半导体科技

PXPG05R010

80-V 11-mΩ GaN Power Transistor (FET)

1 Features

- Higher switching frequency
- Lower switching losses and lower driver power
- Lower conduction
- Zero reverse recovery loss
- RoHS, Pb-free, REACH-compliant

2 Applications

- Automotive lidar/TOF
- 48V servers
- Pulsed power
- Isolated power supplies
- Point of load converters
- Class D audio
- LED lighting
- Low inductance motor drive

3 Description

This is a 80V GaN-on-Si enhancement-mode power transistor in WLCSP with 1.5mm x 1.5mm package size. The properties of GaN allow for high current, high breakdown voltage and high switching frequency.

Parameters	Values	Units
$V_{DS,\ max}$	80	V
$R_{DS(on),\ max}$	11	mΩ
Q_G, typ @V_{DS}=50V	3.5	nC
$I_{D,\ Continuous\ current}$	8.2	A
Q_{OSS} @ 50 V	15	nC

Performance Parameters at Tj = 25 ℃